

/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

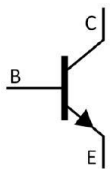
/ Features

P_C , I_C
High P_C and I_C .

/ Applications

2W
2W output amplifier of portable radios in class B push-pull operation.

/ Equivalent Circuit



/ Pinning



PIN1 Collector PIN 2 Base PIN 3 Emitter

/ hFE Classifications & Marking

See Marking Instructions.

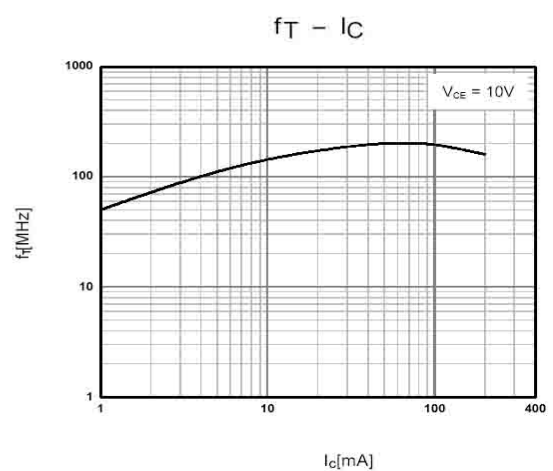
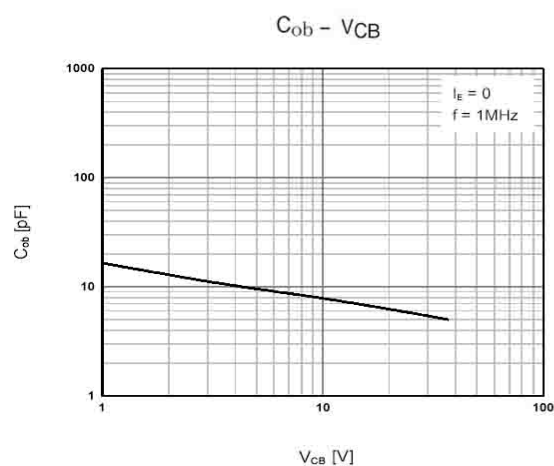
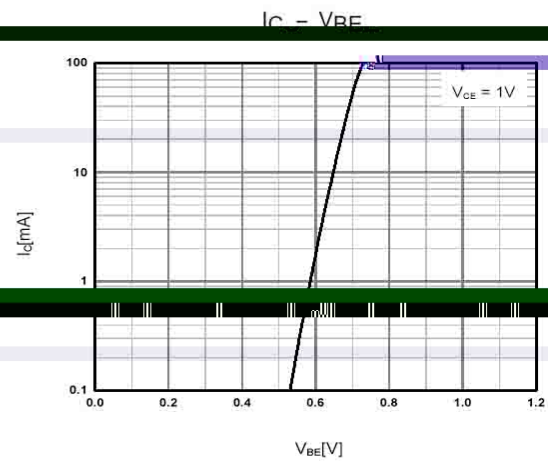
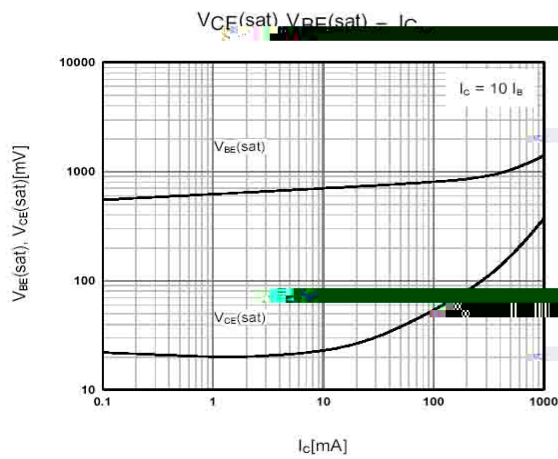
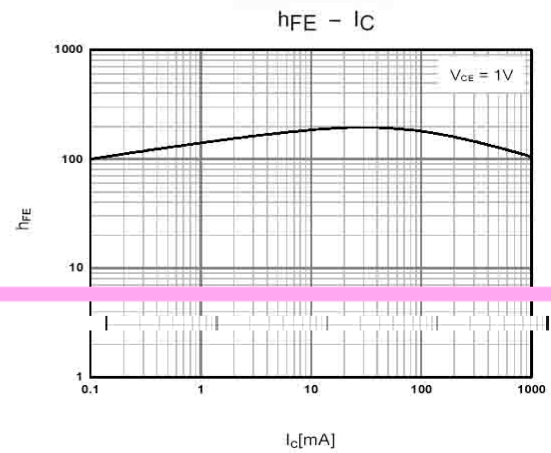
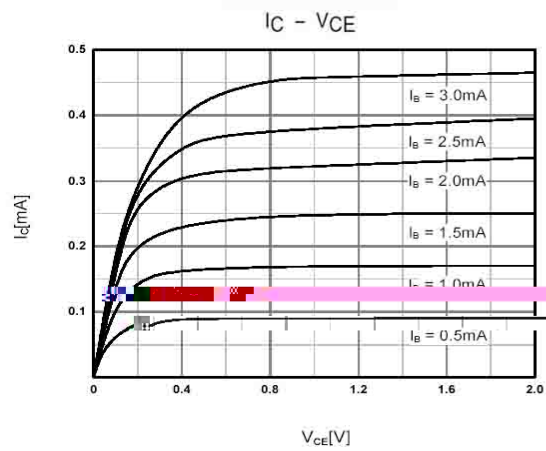
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Base Current - Continuous	I_B	500	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=100mA$	200		350	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=800mA$	40			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=5.0mA$	45			
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=800mA$ $I_B=80mA$		0.28	0.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=800mA$ $I_B=80mA$		0.98	1.2	V
Base-to-Emitter Voltage	V_{BE}	$V_{CE}=1.0V$ $I_C=10mA$		0.66	1.0	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$	100	190		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$ $I_E=0$		9.0		pF

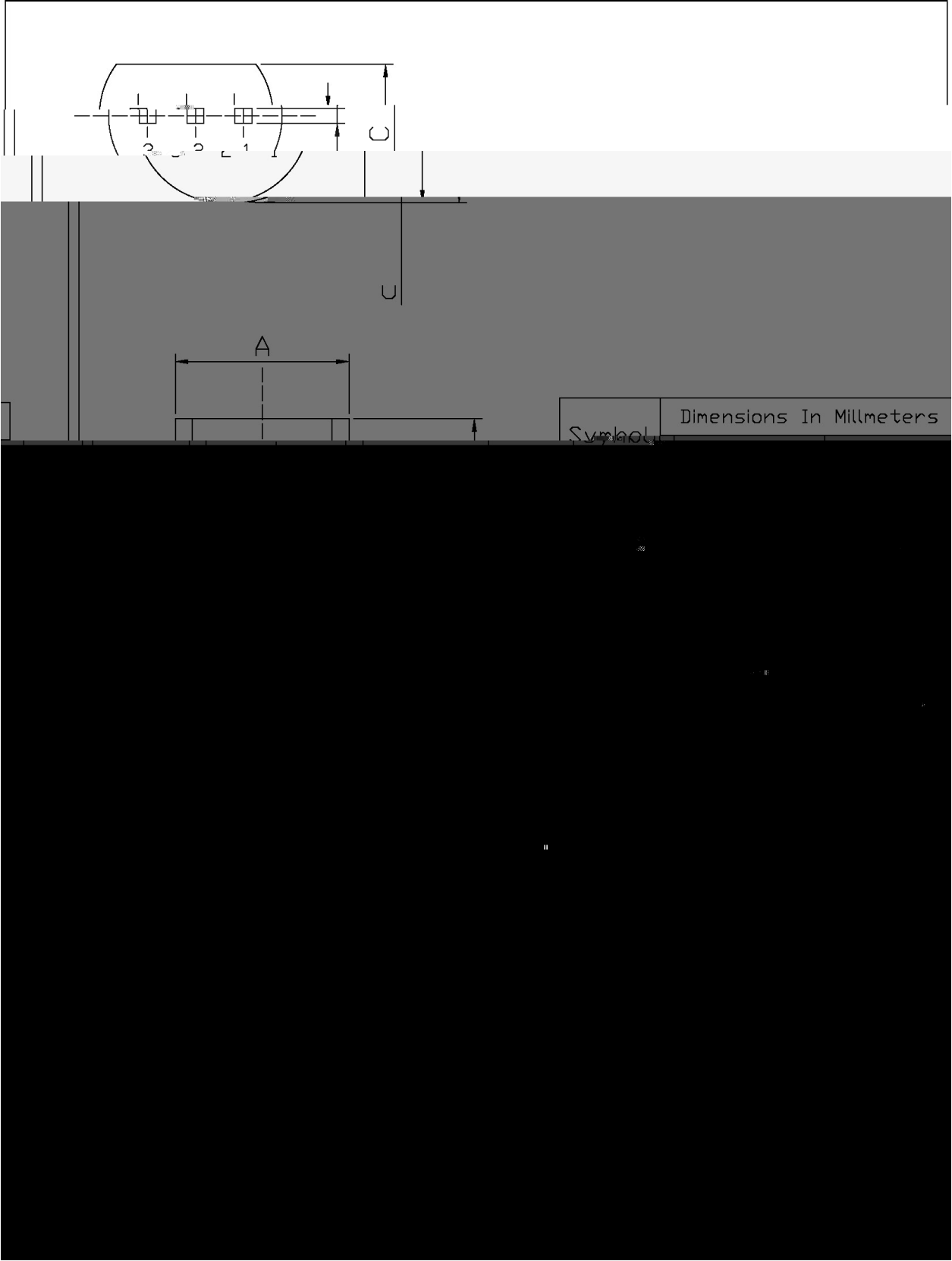
/ Electrical Characteristic Curve



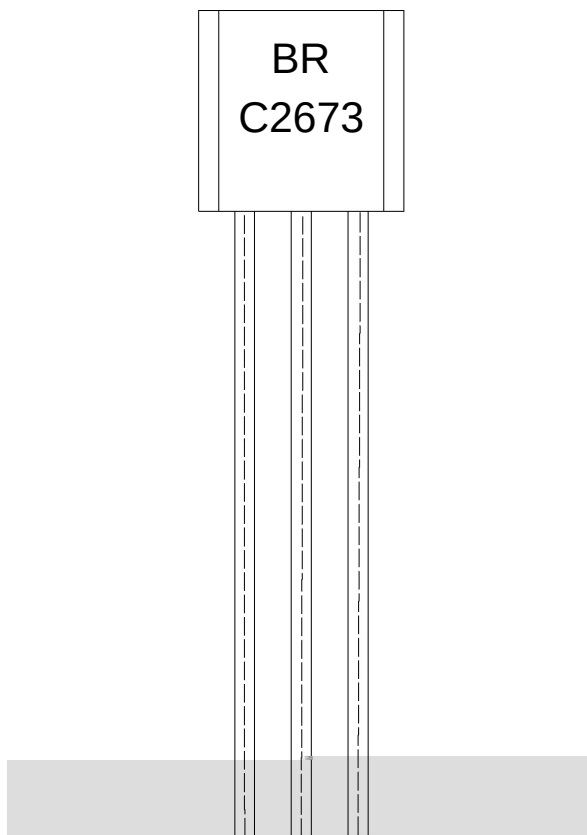
/ Package Dimensions

T0-92

Unit: mm



/ Marking Instructions



BR:

C2673

Note:

BR: Company Code.

C2673: Product Type.

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. | |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension		(unit mm3)

/ Notices